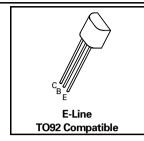
PNP SILICON PLANAR MEDIUM POWER TRANSISTORS

ZTX552 ZTX553

ISSUE 1 - MARCH 94

FEATURES

- * 100 Volt V_{CEO}
- * 1 Amp continuous current
- * P_{tot}=1 Watt



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	ZTX552	ZTX553	UNIT
Collector-Base Voltage	V _{CBO}	-100 -120		٧
Collector-Emitter Voltage	V_{CEO}	-80	-100	٧
Emitter-Base Voltage	V _{EBO}	-	V	
Peak Pulse Current	I _{CM}	-2		Α
Continuous Collector Current	I _C	-1		Α
Power Dissipation: at T _{amb} =25°C derate above 25°C	P _{tot}	1 5.7		W mW/ °C
Operating and Storage Temperature Range	$T_{j:}T_{stg}$	-55 to +200		°C

ELECTRICAL CHARACTERISTICS (at Tamb = 25°C).

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PARAMETER	SYMBOL	ZTX	(552	ZTX553		UNIT	CONDITIONS.			
		MIN.	MAX.	MIN.	MAX.					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-100		-120		V	I _C =-100μA			
Collector-Emitter Sustaining Voltage	V _{CEO(sus)}	-80		-100		V	I _C =-10mA			
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5		-5		V	I _E =-100μA			
Collector Cut-Off Current	I _{CBO}		-0.1		-0.1	μА	V _{CB} =-80V V _{CB} =-100V			
Emitter Cut-Off Current	I _{EBO}		-0.1		-0.1	μΑ	V _{EB} =-4V			
Collector-Emitter Saturation Voltage	V _{CE(sat)}		-0.25		-0.25	V	I _C =-150mA, I _B =-15mA*			
Base-Emitter Saturation Voltage	V _{BE(sat)}		-1.1		-1.1	V	I _C =-150mA, I _B =-15mA*			
Base-Emitter Turn-onn Voltage	V _{BE(on)}		-1.0		-1.0	V	I _C =-150mA, V _{CE} =-10V*			
Static Forward Current Transfer Ratio	h _{FE}	40 10	150	40 10	200		I _C =-150mA, V _{CE} =-10V* I _C =-1A, V _{CE} =-10V*			
Transition Frequency	f _T	150		150		MHz	I _C =-50mA, V _{CE} =-10V f=100MHz			
Output Capacitance	C _{obo}		12		12	MHz	V _{CB} =-10V, f=1MHz			

^{*}Measured under pulsed conditions. Pulse width=300µs. Duty cycle ≤2%

ZTX552 ZTX553

TYPICAL CHARACTERISTICS

